

*B1* 23. (Amended) Structure according to Claim 20, characterized in that the thin layer (2) is made integral with a support (3) through an intermediate conductive surface.

*B2* 26. (Amended) Structure according to Claim 23, characterized in that deposition of conductive bonding materials is associated with said metal interface layer.

*B3* 28. (Amended) Structure according to Claim 22, characterized in that the thin layer (2) is made integral with a support (3) through the use of a brazing material.

*B4* 30. (Amended) Structure according to any one of Claim 20, characterized in that the material of the thin layer (2) is chosen from among SiC, GaAs and InP.

*B5* 31. (Amended) Structure according to Claim 23, characterized in that the support (3) is made of silicon.

*B5*  
*cont*  
Please add claims 32-36 as follows:

32. (New) Structure according to Claim 22, characterized in that the thin layer (2) is made integral with a support (3) through an intermediate conductive interface.

33. (New) Structure according to Claim 25, characterized in that deposition of conductive bonding materials is associated with said metal interface layer.